

## AMENDMENT TO SPECIFICATION

After the title, please insert the following paragraph:

### Related Applications

This application is a divisional application of U.S. Patent Application Serial No. 07/722,479 filed November 28, 2000 which claims priority from continuation-in-part Patent Application Serial No. 09/191,120 filed November 13, 1998, now abandoned, which is incorporated herein by reference.

Please amend the paragraph beginning at line 14 on page 13 as follows:

In the first embodiment, the thickness of the dielectric film 32 is determined so that the tilting of the storage node 22 is effectively prevented and that the storage node 22 has a grate surface area. More specifically, in the first embodiment, the thickness of the dielectric film 32 is set to a given value which is greater than the thickness of the horizontal surface 28 of the storage node 22 and is smaller than the height of the vertical surface 30. Further, the thickness of the dielectric film 32 is determined such that the storage node 22 assumes a desired capacity. The oxide-film etching for reducing the thickness of the dielectric film 22 may be a dry process or a wet process.

Page 19, please amend the paragraph beginning at line 17 as follows.

(In the fortieth step): processing for depositing doped polysilicon 98 (indicated by a broken line and a solid line provided in Fig. 22) into the cylindrical spaces 98 96 and on the remaining oxide film 86; and

Please amend the paragraph beginning at line 3 on page 20 as follows:

(In the forty-second step) : processing for causing the tip end of the storage node 78 to be out from the surface of the oxide film 86 by reducing the thickness of the oxide film 86 interposed among the adjacent storage nodes 78 to a given thickness by means of oxide-film etching. By means of the foregoing processing, the dielectric film 88 for tilt prevention purposes which has a given thickness and is in close contact with the vertical surface 82 of the storage node 78 can be formed around the vertical surface 82. In this embodiment, the thickness of the dielectric film 88 is determined such that the storage node 78 assumes a desired capacity. The oxide-film etching for reducing the thickness of the oxide film 86 may be a dry process or a wet process.

Please amend the paragraph beginning at line 16 on page 24 as follows:

(In the fifty-fourth step) : processing for forming a dielectric film 126 for tilt prevention purpose by etching the oxide film 124 to a given thickness. In this embodiment, the thickness of the dielectric film 126 is determined such that the storage node 106 assumes a desired capacity.

The oxide-film etching for reducing the thickness of the oxide film 124 may be a dry process or a wet process.